

TOSHIBA**MT3S04AU**

TENTATIVE

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

MT3S04AU

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

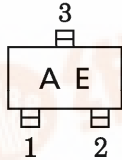
Unit in mm

- Low Noise : Figure : NF = 1.2 dB
- High Gain : Gain = 12.5 dB (f = 1 GHz)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	10	V
Collector-Emitter Voltage	V _{CEO}	5	V
Emitter-Base Voltage	V _{EBO}	2	V
Base Current	I _C	40	mA
Collector Current	I _B	10	mA
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C

MARKING



1. BASE	
2. EMITTER	
3. COLLECTOR	
USM	
JEDEC	—
EIAJ	SC-70
TOSHIBA	2-2E1A

Weight : 0.006 g

MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f _T (1)	V _{CE} = 1 V, I _C = 5 mA	2	5	—	GHz
	f _T (2)	V _{CE} = 3 V, I _C = 7 mA	5	7	—	
Insertion Gain	S _{21e} ² (1)	V _{CE} = 1 V, I _C = 5 mA, f = 1 GHz	—	9.5	—	dB
	S _{21e} ² (2)	V _{CE} = 3 V, I _C = 20 mA, f = 1 GHz	7.5	12.5	—	
Noise Figure	NF (1)	V _{CE} = 1 V, I _C = 5 mA, f = 1 GHz	—	1.3	2.2	dB
	NF (2)	V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	—	1.2	2	

000707EAA2

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	80	—	160	—
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note)	—	0.8	1.15	pF

(Note) : C_{re} is measured by 3 terminal method with capacitance bridge.

CAUTION

This device electrostatic sensitivity. Please handle with caution.